

TO-92 Plastic-Encapsulate Transistors

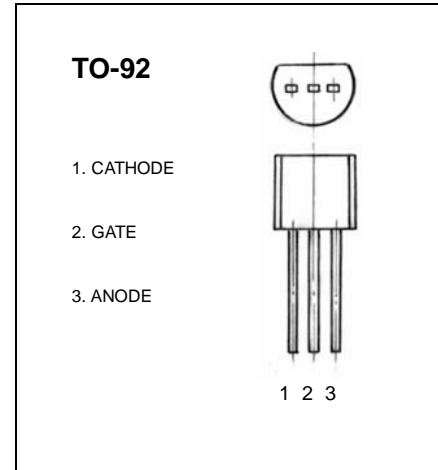
XL1225 Silicon Planar pnpn Thyristor

FEATURES

Current- I_{GT} : 120 μ A

I_{TRMS} : 0.6 A

V_{DRM} : 400 V



Operating and storage junction temperature range

T_J, T_{stg} : -55°C to +150°C

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT	
On state voltage	V_{TM}	$I_{TM}=0.6A$		1.7	V	
Gate trigger voltage	V_{GTF}	$V_{AK}=7V$		0.8	V	
Repetitive peak off-state voltage	V_{DRM}	$I_{DRM}= 10\mu A$	400		V	
Holding current	I_H	$I_{HL}= 20mA, A_v = 7 V$		5	mA	
Gate trigger current	I_{GTF}	$V_{AR}=7V$	A2	5	15	μA
			A1	15	30	μA
			A-1	30	45	μA
			A-2	45	60	μA
			A	60	80	μA
			B	80	120	μA